

a circuit pattern made of an aluminum alloy and provided on an upper main surface of said ceramic substrate and having a thickness 0.4 to 0.6 mm on which said power semiconductor element is held;

A23
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a lower pattern made of said aluminum alloy and provided entirely on a lower main surface of said ceramic substrate opposite to said upper main surface;

a metal base plate made of a copper alloy having a thickness of 3.5 to 5.5 mm positioned opposite to said lower pattern; and

a soldering layer provided between an entire surface of said lower pattern and said metal base plate for forming a joint therebetween.

Please add new Claims 8-12 as follows:

8. (New) A power semiconductor device comprising:

a ceramic substance having a thickness of 0.5 to 1 mm;

A24
a power semiconductor element;

a circuit pattern made of aluminum alloy and provided on an upper main surface of said ceramic substrate and having a thickness of 0.4 to 0.6 mm on which said power semiconductor element is held;

a lower pattern made of said aluminum alloy and provided entirely on a lower main surface of said ceramic substrate opposite to said upper main surface;

a metal base plate made of copper alloy having a thickness of 3.5 to 5.5 mm positioned opposite to said lower pattern;

a soldering layer of uniform thickness provided between an entire surface of said lower pattern and said metal base plate for forming a joint therebetween; and

a wire bump provided on said lower pattern to establish said uniform thickness.